VS-HFA06TB120S-M3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 6 A



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PRIMARY CHARACTERISTICS					
I _{F(AV)}	6 A				
V _R	1200 V				
V _F at I _F	2.4 V				
t _{rr} (typ.)	26 ns				
T _J max.	150 °C				
Package	D ² PAK (TO-263AB)				
Circuit configuration	Single				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- HALOGEN Meets MSL level 1, per J-STD-020, LF maximum FREE peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA06TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		1200	V			
Maximum continuous forward current	I _F	T _C = 100 °C	6				
Single pulse forward current	I _{FSM}		80	А			
Maximum repetitive forward current	I _{FRM}		24				
Maximum power dissipation	р	T _C = 25 °C	62.5	W			
	P _D	T _C = 100 °C	25	vv			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

Revision: 27-Oct-17



COMPLIANT



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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	BOL TEST CONDITIONS		TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage	V _{FM}	I _F = 6.0 A	-	2.7	3.0	v			
		I _F = 12 A	-	3.5	3.9	7			
		I _F = 6.0 A, T _J = 125 °C	-	2.4	2.8				
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.26	5.0				
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	110	500	μA			
Junction capacitance	CT	V _R = 200 V	-	9.0	14	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	A/μs, V _R = 30 V	-	26	-			
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	53	80	ns		
	t _{rr2}	T _J = 125 °C	I _F = 6.0 A dI _F /dt = 200 A/µs V _R = 200 V	-	87	130			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.4	8.0	A nC		
Feak recovery current	I _{RRM2}	T _J = 125 °C		-	5.0	9.0			
Poverao racoveru obergo	Q _{rr1}	T _J = 25 °C		-	116	320			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	233	585	ne		
Peak rate of recovery current during $t_{\rm b}$	dl _{(rec)M} /dt1	T _J = 25 °C		-	180	-	A/µs		
	dl _{(rec)M} /dt2	T _J = 125 °C		-	100	-			

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	2.0			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Marking device		Case style D ² PAK (TO-263AB)		HFA06	TB120S			



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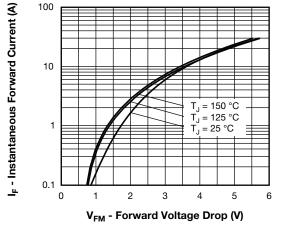


Fig. 1 - Typical Forward Voltage Drop Characteristics

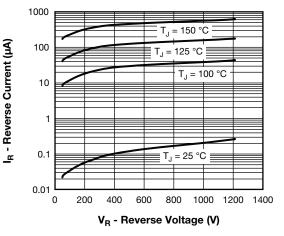


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

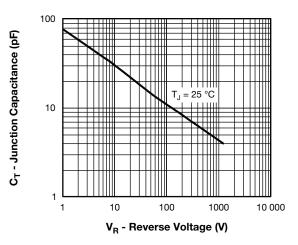


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

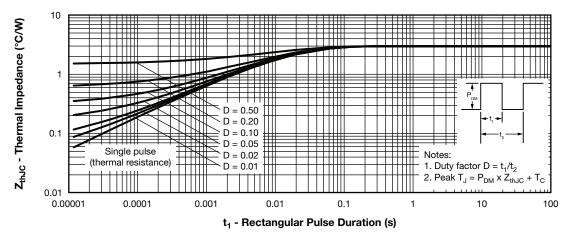
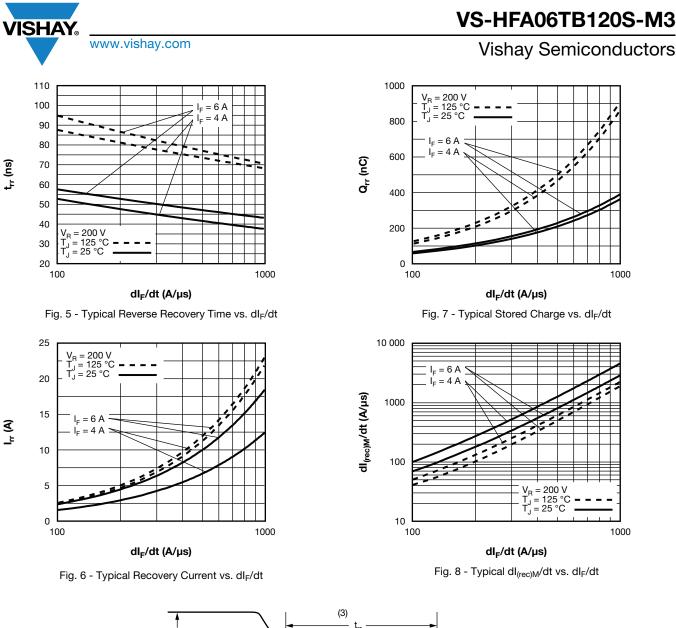


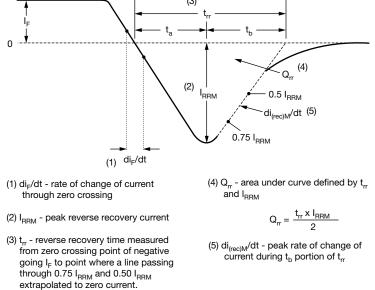
Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

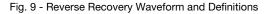
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 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com

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Device code	vs-	HF	Α	06	тв	120	S	L	-M3
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			,	niconduo ຈັດ	ctors pro	oduct			
	2		KFRED [®]	-					
	3 ·	- Pro	cess de	signator	: A = ele	ectron ir	radiate	d	
	4	- Cur	rent rati	ng (06 =	= 6 A)				
	5	· Pac	kage ou	utline (T	B = TO-	220, 2 l	eads)		
	6	· Vol	age rati	ng (120	= 1200	V)			
	7.	- S =	D ² PAK	(TO-26	3AB)				
	8 -	• N	one = tu	be (50 p	oieces)				
		۰L	= tape a	and reel	(left orie	ented)			
		• R	= tape a	and reel	(right o	riented)			
	9 -	- Env	ironmer	ntal digit	:				
		-M3	8 = halog	gen-free	, RoHS	-compli	ant, and	d termin	ations I

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA06TB120S-M3	50	1000	Antistatic plastic tube					
VS-HFA06TB120SR-M3	800	800	13" diameter reel					
VS-HFA06TB120SL-M3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

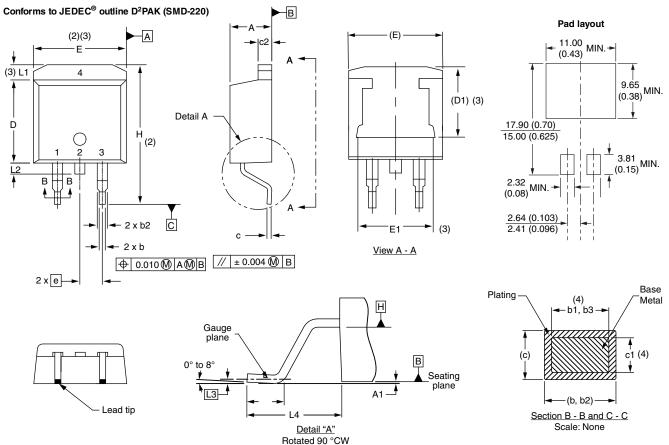
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D²PAK

DIMENSIONS in millimeters and inches

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SYMBOL	MILLIMETERS		INCHES		NOTES
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS		INCHES		NOTES
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

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Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

Controlling dimension: inches (6)

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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